# Memory FRAM

# 64 K (8 K $\times$ 8) Bit I<sup>2</sup>C

# MB85RC64A

# DESCRIPTION

The MB85RC64A is an FRAM (Ferroelectric Random Access Memory) chip in a configuration of 8,192 words  $\times$  8 bits, using the ferroelectric process and silicon gate CMOS process technologies for forming the nonvolatile memory cells.

Unlike SRAM, the MB85RC64A is able to retain data without using a data backup battery.

The read/write endurance of the nonvolatile memory cells used for the MB85RC64A has improved to be at least 10<sup>12</sup> cycles, significantly outperforming Flash memory and E<sup>2</sup>PROM in the number.

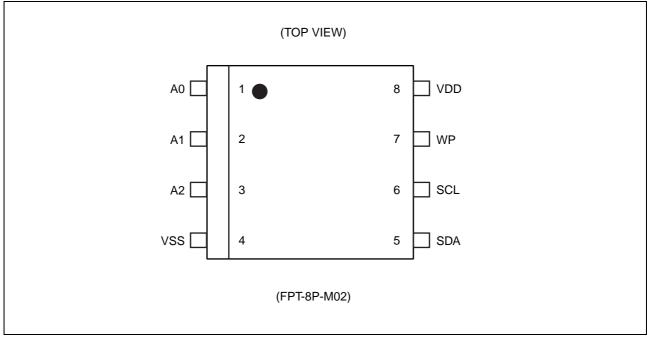
The MB85RC64A does not need a polling sequence after writing to the memory such as the case of Flash memory or E<sup>2</sup>PROM.

# ■ FEATURES

<ul> <li>Bit configuration</li> </ul>	: 8,192 words $\times$ 8 bits
<ul> <li>Two-wire serial interface</li> </ul>	: Fully controllable by two ports: serial clock (SCL) and serial data (SDA).
<ul> <li>Operating frequency</li> </ul>	: 1 MHz (Max)
<ul> <li>Read/write endurance</li> </ul>	: 10 <sup>12</sup> times / byte
<ul> <li>Data retention</li> </ul>	: 10 years ( + 85 °C), 95 years ( + 55 °C), over 200 years ( + 35 °C)
Operating power supply voltage	: 2.7 V to 3.6 V
<ul> <li>Low power consumption</li> </ul>	: Operating power supply current 250 $\mu$ A (Typ @1 MHz)
	Standby current 5 μA (Typ)
Operation ambient temperature	range : - 40 °C to + 85 °C
Package	: 8-pin plastic SOP (FPT-8P-M02)
	RoHS compliant



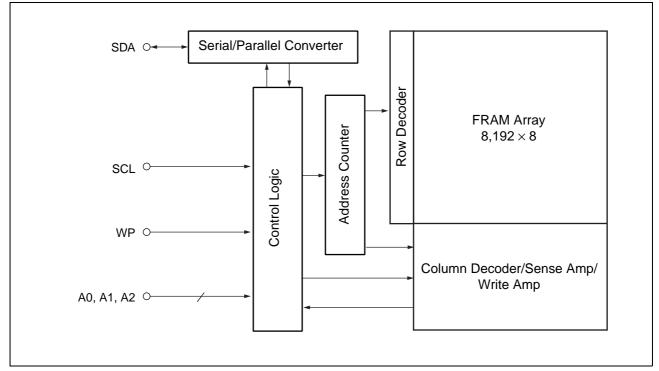
# ■ PIN ASSIGNMENT



# ■ PIN FUNCTIONAL DESCRIPTIONS

Pin Number	Pin Name	Functional Description
1 to 3	A0 to A2	Device Address pins The MB85RC64A can be connected to the same data bus up to 8 devices. Device addresses are used in order to identify each of these devices. Connect these pins to VDD pin or VSS pin externally. Only if the combination of VDD and VSS pins matches a Device Address Code inputted from the SDA pin, the device operates. In the open pin state, A0, A1, and A2 pins are internally pulled- down and recognized as the "L" level.
4	VSS	Ground pin
5	SDA	Serial Data I/O pin This is an I/O pin which performs bidirectional communication for both memory address and writing/reading data. It is possible to connect multiple devices. It is an open drain output, so a pull-up resistor is required to be connected to the ex- ternal circuit.
6	SCL	Serial Clock pin This is a clock input pin for input/output timing serial data. Data is sampled on the rising edge of the clock and output on the falling edge.
7	WP	Write Protect pin When the Write Protect pin is the "H" level, the writing operation is disabled. When the Write Protect pin is the "L" level, the entire memory region can be overwritten. The reading operation is always enabled regardless of the Write Protect pin input level. The write protect pin is internally pulled down to VSS pin, and that is recognized as the "L" level (write enabled) when the pin is the open state.
8	VDD	Supply Voltage pin

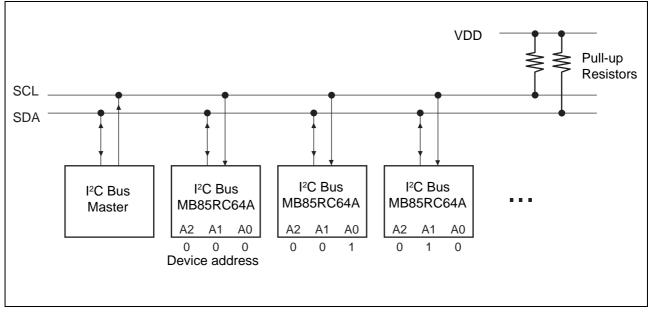
## BLOCK DIAGRAM



## ■ I<sup>2</sup>C (Inter-Integrated Circuit)

The MB85RC64A has the two-wire serial interface; the l<sup>2</sup>C bus,and operates as a slave device. The l<sup>2</sup>C bus defines communication roles of "master" and "slave" devices, with the master side holding the authority to initiate control. Furthermore, an l<sup>2</sup>C bus connection is possible where a single master device is connected to multiple slave devices in a party-line configuration. In this case, it is necessary to assign a unique device address to the slave device, the master side starts communication after specifying the slave to communicate by addresses.





## ■ I<sup>2</sup>C COMMUNICATION PROTOCOL

The I<sup>2</sup>C bus is a two wire serial interface that uses a bidirectional data bus (SDA) and serial clock (SCL). A data transfer can only be initiated by the master, which will also provide the serial clock for synchronization. The SDA signal should change while SCL is the "L" level. However, as an exception, when starting and stopping communication sequence, SDA is allowed to change while SCL is the "H" level.

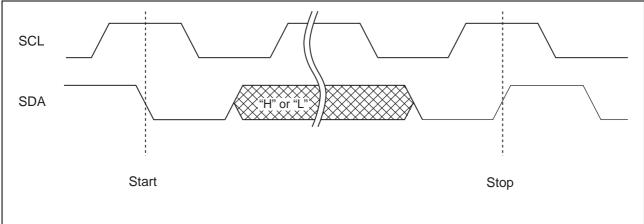
#### • Start Condition

To start read or write operations by the I<sup>2</sup>C bus, change the SDA input from the "H" level to the "L" level while the SCL input is in the "H" level.

• Stop Condition

To stop the I<sup>2</sup>C bus communication, change the SDA input from the "L" level to the "H" level while the SCL input is in the "H" level. In the reading operation, inputting the stop condition finishes reading and enters the standby state. In the writing operation, inputting the stop condition finishes inputting the rewrite data and enters the standby state.

#### • Start Condition, Stop Condition

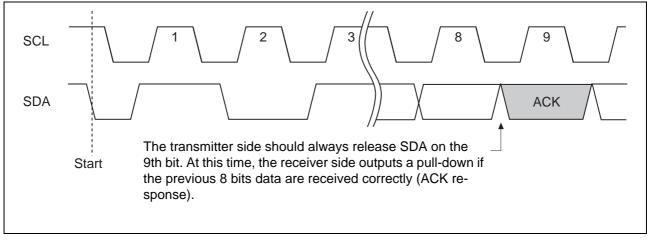


Note : At the write operation, the FRAM device does not need the programming wait time (twc) after issuing the Stop Condition.

# ACKNOWLEDGE (ACK)

In the I<sup>2</sup>C bus, serial data including address or memory information is sent in units of 8 bits. The acknowledge signal indicates that every 8 bits of the data is successfully sent and received. The receiver side usually outputs the "L" level every time on the 9th SCL clock after each 8 bits are successfully transmitted and received. On the transmitter side, the bus is temporarily released to Hi-Z every time on this 9th clock to allow the acknowledge signal to be received and checked. During this Hi-Z-released period, the receiver side pulls the SDA line down to indicate the "L" level that the previous 8 bits communication is successfully received.

In case the slave side receives Stop condition before sending or receiving the ACK "L" level, the slave side stops the operation and enters to the standby state. On the other hand, the slave side releases the bus state after sending or receiving the NACK "H" level. The master side generates Stop condition or Start condition in this released bus state.



• Acknowledge timing overview diagram

## DEVICE ADDRESS WORD (Slave address)

Following the start condition, the master sends the 8 bits device address word to start  $I^2C$  communication. The device address word (8 bits) consists of a device Type code (4 bits), device address code (3 bits), and a read/write code (1 bit).

• Device Type Code (4 bits)

The upper 4 bits of the device address word are a device type code that identifies the device type, and are fixed at "1010" for the MB85RC64A.

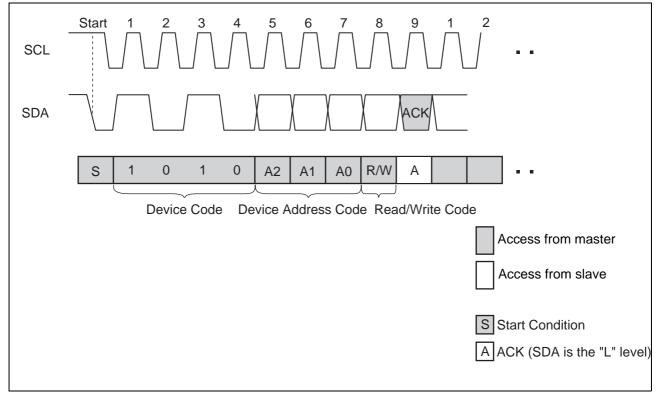
• Device Address Code (3 bits)

Following the device type code, the 3 bits of the device address code are input in order of A2, A1, and A0. The device address code identifies one device from up to eight devices connected to the bus. Each MB85RC64A is given a unique 3 bits code on the device address pin (external hardware pin A2, A1, and A0). The slave only responds if the received device address code is equal to this unique 3 bits code.

• Read/Write Code (1 bit)

The 8th bit of the device address word is the R/W (read/write) code. When the R/W code is "0", a write operation is enabled, and the R/W code is "1", a read operation is enabled for the MB85RC64A.

It turns to a stand-by state if the device code is not "1010" or device address code does not equal to pins A2, A1, and A0.



#### Device Address Word

## ■ DATA STRUCTURE

In the I<sup>2</sup>C bus, the acknowledge "L" level is output on the 9th bit by a slave, after the 8 bits of the device address word following the start condition are input by a master. After confirming the acknowledge response by the master, the master outputs 8bits  $\times$  2 memory address to the slave. When the each memory address input ends, the slave again outputs the acknowledge "L" level. After this operation, the I/O data follows in units of 8 bits, with the acknowledge "L" level output after every 8 bits.

It is determined by the R/W code whether the data line is driven by the master or the slave. However, the clock line shall be driven by the master. For a write operation, the slave will accept 8 bits from the master, then send an acknowledge. If the master detects the acknowledge, the master will transfer the next 8 bits. For a read operation, the slave will place 8 bits on the data line, then wait for an acknowledge from the master.

## ■ FRAM ACKNOWLEDGE -- POLLING NOT REQUIRED

The MB85RC64A performs write operations at the same speed as read operations, so any waiting time for an ACK polling\* does not occur. The write cycle takes no additional time.

\*: In E<sup>2</sup>PROM, the Acknowledge Polling is performed as a progress check whether rewriting is executed or not. It is normal to judge by the 9th bit of Acknowledge whether rewriting is performed or not after inputting the start condition and then the device address word (8 bits) during rewriting.

## ■ WRITE PROTECT (WP)

The entire memory array can be write protected using the Write Protect pin. When the Write Protect pin is set to the "H" level, the entire memory array will be write protected. When the Write Protect pin is the "L" level, entire memory array will be rewritten. Reading is allowed regardless of the WP pin's "H" level or "L" level.

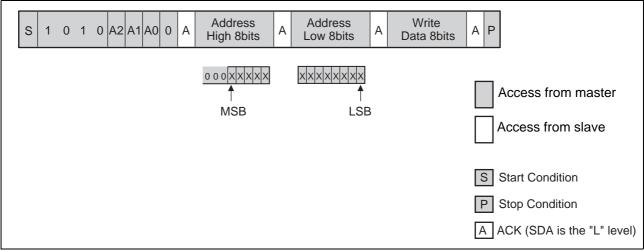
Note : The Write Protect pin is pulled down internally to VSS pin, therefore if the Write Protect pin is open, the pin status is detected as the "L" level (write enabled).



## COMMAND

#### • Byte Write

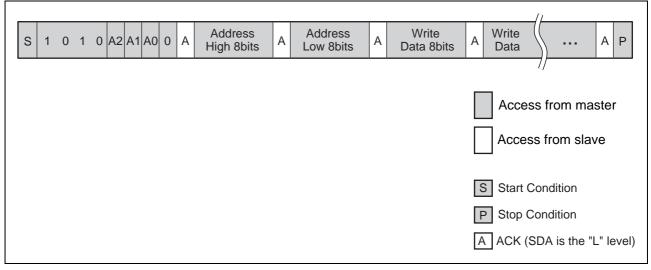
If the device address word (R/W "0" input ) is sent following the start condition, the slave responds with an ACK. After this ACK, write addresses and data are sent in the same way, and the write ends by generating a stop condition at the end.



Note : In the MB85RC64A, input "000" as the upper 3 bits of the MSB.

Page Write

If additional 8 bits are continuously sent after the same command (except stop condition) as Byte Write, a page write is performed. The memory address rolls over to first memory address (0000H) at the end of the address. Therefore, if more than 8 Kbytes are sent, the data is overwritten in order starting from the start of the memory address that was written first. Because FRAM performs the high-speed write operations, the data will be written to FRAM right after the ACK response finished.



Note : It is not necessary to take a period for internal write operation cycles from the buffer to the memory after the stop condition is generated.

#### • Current Address Read

When the previous write or read operation finishes successfully up to the stop condition and assumes the last accessed address is "n", then the address at "n+1" is read by sending the following command unless turning the power off. If the memory address is last address, the address counter will roll over to 0000<sub>H</sub>. The current address in memory address buffer is undefined immediately after the power is turned on.

	Access from master
	Access from slave
(n+1) address	S Start Condition
S 1 0 1 0 A2 A1 A0 1 A Read Data 8bits N P	P Stop Condition
	A ACK(SDA is the "L" level)
	N NACK (SDA is the "H" level)

#### • Random Read

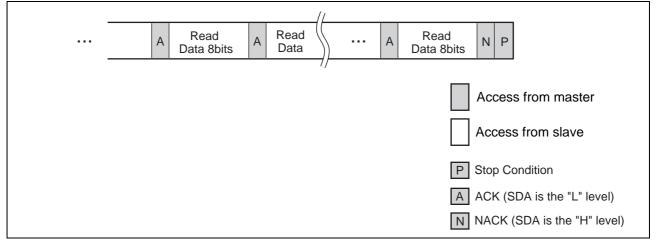
The one byte of data from the memory address saved in the memory address buffer can be read out synchronously to SCL by specifying the address in the same way as for a write, and then issuing another start condition and sending the Device Address Word (R/W "1" input).

The final NACK is issued by the receiver that receives the data. In this case, this bit is issued by the master side.

S	1	0	1	0 A2	2 A'			Addr High	A	Addres .ow 8b	A	S	1	0	1	0 A	2 A		1	A	[	Rea Data 8		N	Р
																	_								
																		Acc	ess	s fro	m	mas	ter		
																		Acc	ess	s fro	m	slave	e		
																	S	Star	t Co	ondi	tior	n			
																	Ρ	Stop	o Co	ondi	tior	n			
																[	A	ACł	< (S	DA	is t	the "L	lev	el)	
																	N	NAC	CK (	(SD/	A is	s the	"H" le	evel	)

• Sequential Read

Data can be received continuously following the Device address word (R/W "1" input) after specifying the address in the same way as for Random Read. If the read reaches the end of address, the internal read address automatically rolls over to first memory address 0000H and keeps reading.

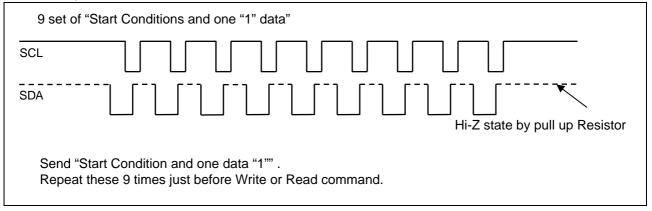


# ■ SOFTWARE RESET SEQUENCE OR COMMAND RETRY

In case the malfunction has occurred after power on, the master side stopped the I<sup>2</sup>C communication during processing, or unexpected malfunction has occurred, execute the following (1) software recovery sequence just before each command, or (2) retry command just after failure of each command.

#### (1) Software Reset Sequence

Since the slave side may be outputting "L" level, do not force to drive "H" level, when the master side drives the SDA port. This is for preventing a bus conflict. The additional hardware is not necessary for this software reset sequence.



## (2) Command Retry

Command retry is useful to recover from failure response during I<sup>2</sup>C communication.

# ■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Ra	Unit		
Farameter	Symbol	Min	Max	Unit	
Power supply voltage*	Vdd	- 0.5	+4.0	V	
Input voltage*	VIN	- 0.5	$V_{DD} + 0.5 \ ( \le 4.0 )$	V	
Output voltage*	Vout	- 0.5	$V_{DD} + 0.5 \ ( \le 4.0 )$	V	
Operation ambient temperature	TA	- 40	+ 85	°C	
Storage temperature	Tstg	- 55	+ 125	°C	

\*: These parameters are based on the condition that VSS is 0 V.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

## RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol		Unit		
Farameter	Symbol	Min	Тур	Max	Onic
Power supply voltage*	Vdd	2.7	3.3	3.6	V
"H" level input voltage*	Vін	$V_{DD}  imes 0.8$	_	$\begin{array}{l} V_{\text{DD}} + 0.5 \\ (\leq 4.0) \end{array}$	V
"L" level input voltage*	VIL	- 0.5	—	+ 0.6	V
Operation ambient temperature	TA	- 40		+ 85	°C

\*: These parameters are based on the condition that VSS is 0 V.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure. No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact

on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

# ELECTRICAL CHARACTERISTICS

## 1. DC Characteristics

## (within recommended operating conditions)

Parameter	Symbol	Condition	Value			
Farameter	Symbol	Min	Тур	Max	Unit	
Input leakage current	lu	SCL, SDA = 0 V to $V_{DD}$			1	μΑ
Output leakage current	Ilo	SDA = 0 V to V <sub>DD</sub>			1	μΑ
Operating power supply current	lod	SCL = 1 MHz		250	375	μΑ
Standby current IsB		$      SCL, SDA = V_{DD} \\ A0, A1, A2, WP = 0 V or V_{DD} $		5	20	μΑ
"L" level output voltage	Vol	lo∟= 3 mA			0.4	V
Input resistance for	Rin	VIN = VIL (Max)	50			kΩ
WP, A0, A1 and A2	I NIN	$V_{IN} = V_{IH}$ (Min)	1			MΩ

## 2. AC Characteristics

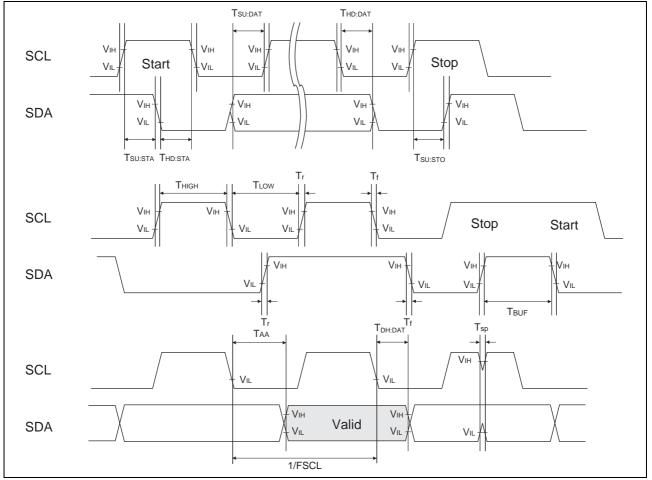
		Value									
Parameter	Symbol	Standa	rd Mode	Fast	Mode	Fast Mo	de Plus	Unit			
		Min	Max	Min	Max	Min	Max				
SCL clock frequency	FSCL	0	100	0	400	0	1000	kHz			
Clock high time	Тнідн	4000		600		400		ns			
Clock low time	TLOW	4700		1300		600		ns			
SCL/SDA rising time	Tr		1000		300		300	ns			
SCL/SDA falling time	Tf		300	_	300		100	ns			
Start condition hold	THD:STA	4000		600		250		ns			
Start condition setup	TSU:STA	4700		600		250		ns			
SDA input hold	THD:DAT	0		0		0		ns			
SDA input setup	TSU:DAT	250		100		100		ns			
SDA output hold	TDH:DAT	0		0		0		ns			
Stop condition setup	Tsu:sto	4000		600	_	250	—	ns			
SDA output access after SCL falling	ΤΑΑ		3000	_	900		550	ns			
Pre-charge time	TBUF	4700	-	1300	-	500		ns			
Noise suppression time (SCL and SDA)	Tsp	_	50		50	_	50	ns			

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AC characteristics were measured under the following measurement conditions.

Power supply voltage	: 2.7 V to 3.6 V
Operation ambient temperature	: – 40 °C to $+85$ °C
Input voltage magnitude	: 0.3 V to 2.7 V
Input rising time	: 5 ns
Input falling time	: 5 ns
Input judge level	: Vdd/2
Output judge level	: Vdd/2

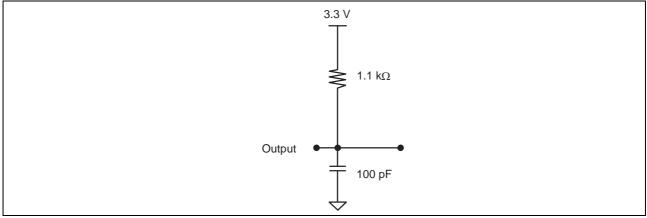
# 3. AC Timing Definitions



## 4. Pin Capacitance

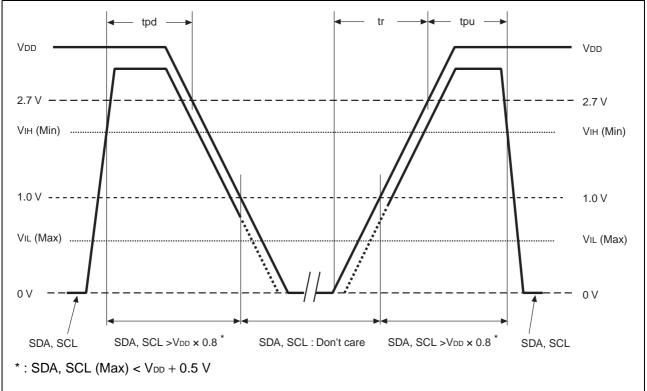
Parameter	Symbol	Conditions		Value		Unit	
Parameter Symbol		Conditions	Min	Тур	Min	Unit	
I/O capacitance	Cı/o	$V_{DD} = V_{IN} = V_{OUT} = 0 V,$			15	pF	
Input capacitance	CIN	$f = 1 \text{ MHz}, T_A = +25 \ ^{\circ}\text{C}$			15	pF	

## 5. AC Test Load Circuit



# POWER ON/OFF SEQUENCE

If  $V_{DD}$  falls down below 2.0V,  $V_{DD}$  is required to be started from 0V to prevent malfunctions when the power is turned on again.



Parameter	Symbol	Va	Unit		
Faiametei	Symbol	Min	Max	Onit	
SDA, SCL level hold time during power down	tpd	85	—	ns	
SDA, SCL level hold time during power up	tpu	85		ns	
Power supply rising time	tr	10		μs	

If the device does not operate within the specified conditions of read cycle, write cycle or power on/off sequence, memory data can not be guaranteed.

# ■ FRAM CHARACTERISTICS

ltem	Min	Max	Unit	Parameter
Read/Write Endurance*1	Write Endurance <sup>*1</sup> 10 <sup>12</sup>			Operation Ambient Temperature $T_A = +85 \ ^{\circ}C$
10 —		Operation Ambient Temperature $T_A = +85 \ ^{\circ}C$		
Data Retention*2	95	_	Years	Operation Ambient Temperature $T_A = +55 \ ^{\circ}C$
	≥ 200	_		Operation Ambient Temperature $T_A = +35 \ ^{\circ}C$

\*1 : Total number of reading and writing defines the minimum value of endurance, as an FRAM memory operates with destructive readout mechanism.

\*2 : Minimun values define retention time of the first reading/writing data right after shipment, and these values are calculated by qualification results.

# NOTE ON USE

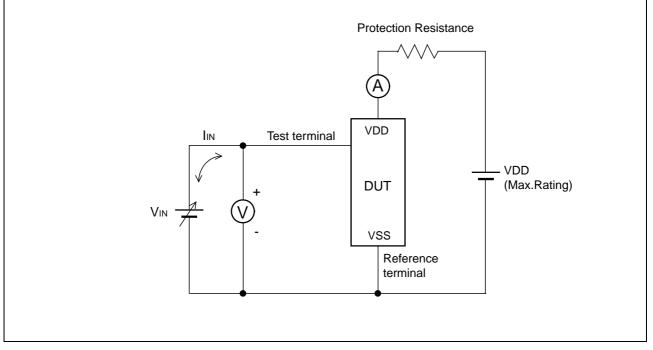
- Data written before performing IR reflow is not guaranteed after IR reflow.
- During the access period from the start condition to the stop condition, keep the level of WP, A0, A1, and A2 pins to the "H" level or the "L" level.



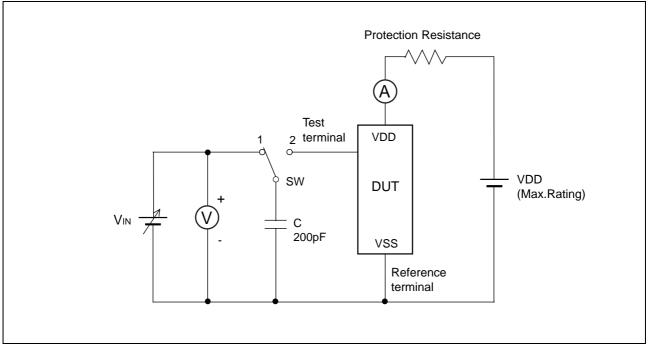
## ■ ESD AND LATCH-UP

Test	DUT	Value
ESD HBM (Human Body Model) JESD22-A114 compliant		≥  2000 V
ESD MM (Machine Model) JESD22-A115 compliant		≥  200 V
ESD CDM (Charged Device Model) JESD22-C101 compliant		
Latch-Up (I-test) JESD78 compliant	MB85RC64APNF-G-JNE1	
Latch-Up (V <sub>supply</sub> overvoltage test) JESD78 compliant	_	
Latch-Up (Current Method) Proprietary method		_
Latch-Up (C-V Method) Proprietary method		_

• Current method of Latch-Up Resistance Test



Note : The voltage V<sub>IN</sub> is increased gradually and the current IIN of 300 mA at maximum shall flow. Confirm the latch up does not occur under  $I_{IN} = \pm 300$  mA. In case the specific requirement is specified for I/O and  $I_{IN}$  cannot be 300 mA, the voltage shall be increased to the level that meets the specific requirement. • C-V method of Latch-Up Resistance Test



Note Charge voltage alternately switching 1 and 2 approximately 2 sec interval. This switching process is considered as one cycle.

Repeat this process 5 times. However, if the latch-up condition occurs before completing 5 times, this test must be stopped immediately.

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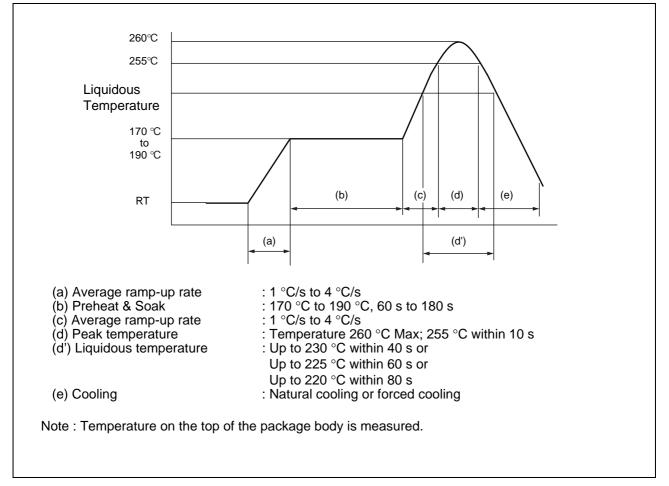
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# ■ REFLOW CONDITIONS AND FLOOR LIFE

Item	Condition				
Method	IR (infrared	reflow), Convection			
Times		2			
	Before unpacking Please use within 2 years after product				
	From unpacking to 2nd reflow	Within 8 days			
Floor life	In case over period of floor life	Baking with 125 °C+/-3 °C for 24hrs+2hrs/-0hrs is required. Then please use within 8 days. (Please remember baking is up to 2 times)			
Floor life condition	Between 5 °C and 30 °C and also below 70%RH required. (It is preferred lower humidity in the required temp range.)				

#### **Reflow Profile**



# RESTRICTED SUBSTANCES

This product complies with the regulations below (Based on current knowledge as of November 2011).

- EU RoHS Directive (2002/95/EC)
- China RoHS (Administration on the Control of Pollution Caused by Electronic Information Products (电子信息产品污染控制管理办法))
- Vietnam RoHS (30/2011/TT-BCT)

Restricted substances in each regulation are as follows.

Substances	Threshold	Contain status*
Lead and its compounds	1,000 ppm	О
Mercury and its compounds	1,000 ppm	О
Cadmium and its compounds	100 ppm	О
Hexavalent chromium compound	1,000 ppm	О
Polybrominated biphenyls (PBB)	1,000 ppm	О
Polybrominated diphenyl ethers (PBDE)	1,000 ppm	О

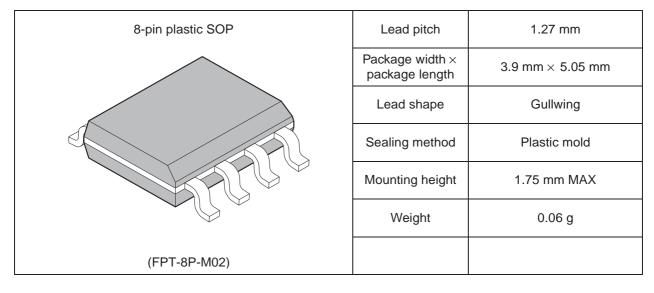
\* : The mark of "O" shows below a threshold value.

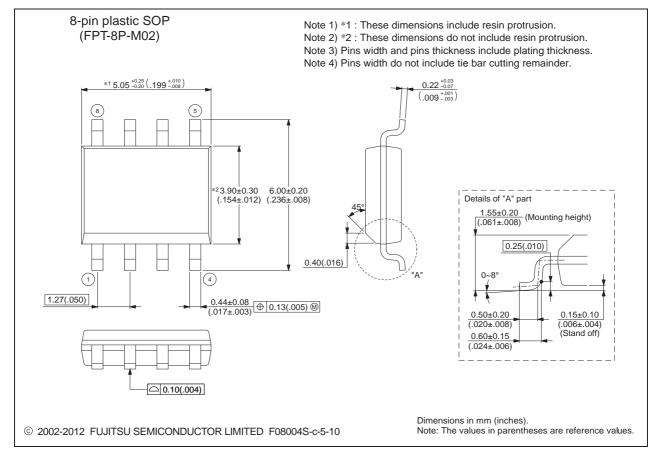
# ■ ORDERING INFORMATION

Part number	Package	Shipping form	Minimum shipping quantity
MB85RC64APNF-G-JNE1	NF-G-JNE1 8-pin, plastic SOP (FPT-8P-M02) Tube		1
MB85RC64APNF-G-JNERE1	8-pin, plastic SOP (FPT-8P-M02)	Embossed Carrier tape	1500



# ■ PACKAGE DIMENSION

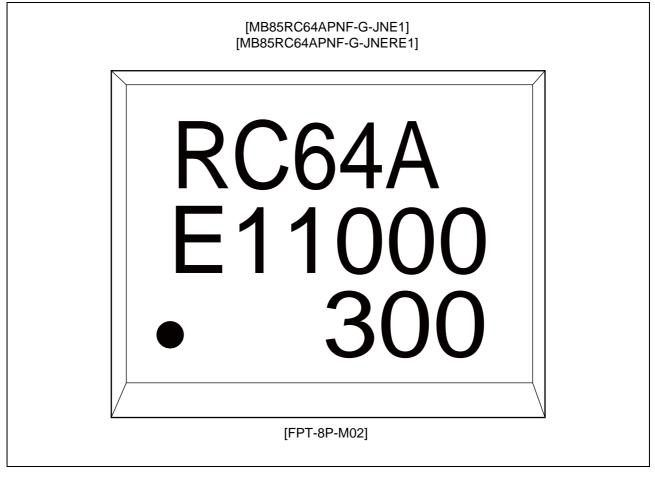




Please check the latest package dimension at the following URL. http://edevice.fujitsu.com/package/en-search/

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## ■ MARKING



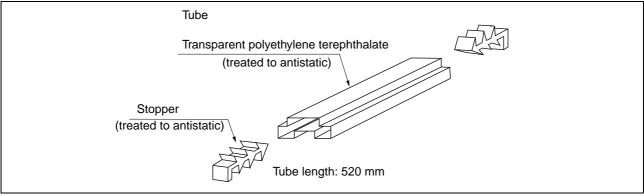


# PACKING INFORMATION

## 1. Tube

## 1.1 Tube Dimensions

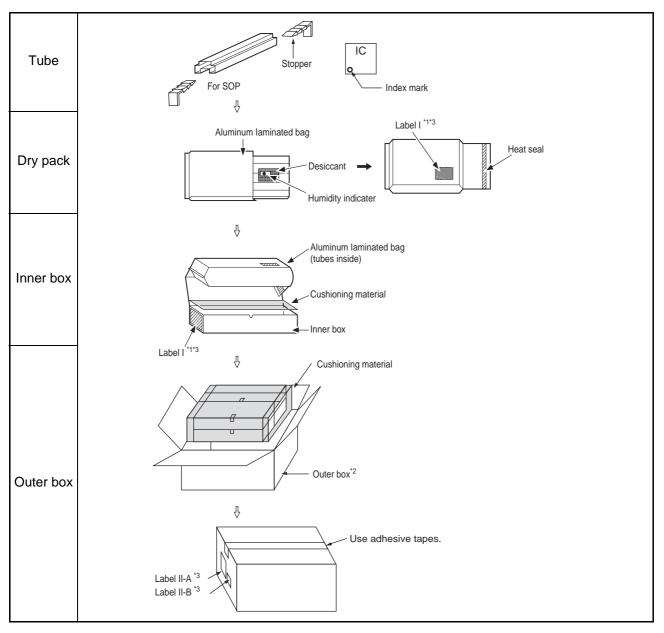
Tube/stopper shape



## Tube cross-sections and Maximum quantity

		Ν	laximum qua	antity
Package form	Package code	pcs/ tube	pcs/inner box	pcs/outer box
SOP, 8, plastic (2)	FPT-8P-M02	95	7600	30400
©2006-2010 FUJITSU SEMICONDUCTOR LIMITED F08008-SET1-PET:FJ99L-0022-E0008-1-K-3				
t = 0.5 Transparent polyethylene terephthalate				

(Dimensions in mm)



#### 1.2 Tube Dry pack packing specifications

\*1: For a product of witch part number is suffixed with "E1", a " G (R)" marks is display to the moisture barrier bag and the inner boxes.

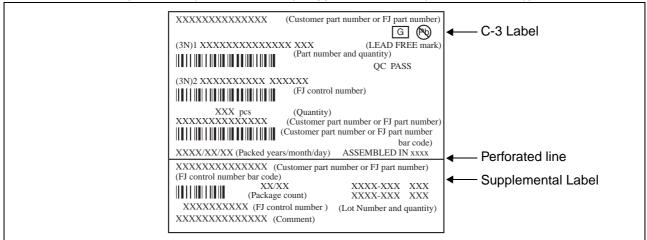
\*2: The space in the outer box will be filled with empty inner boxes, or cushions, etc.

\*3: Please refer to an attached sheet about the indication label.

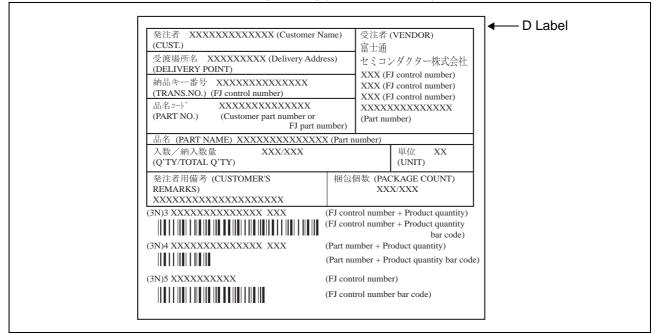
Note: The packing specifications may not be applied when the product is delivered via a distributer.

## 1.3 Product label indicators

Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



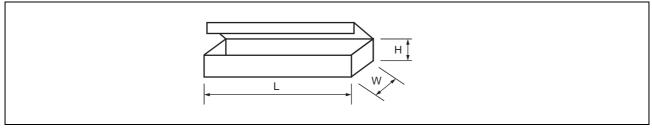
#### Label II-B: Outer boxes product indicate

XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX	Part number)		
(Lot Number) XXXX-XXX XXXX-XXX	(Count) X箱 X箱 計	(Quantity) XXX 個 XXX 個 XXX 個	

Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

## 1.4 Dimensions for Containers

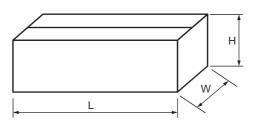
#### (1) Dimensions for inner box



L	W	Н
540	125	75

(Dimensions in mm)

## (2) Dimensions for outer box

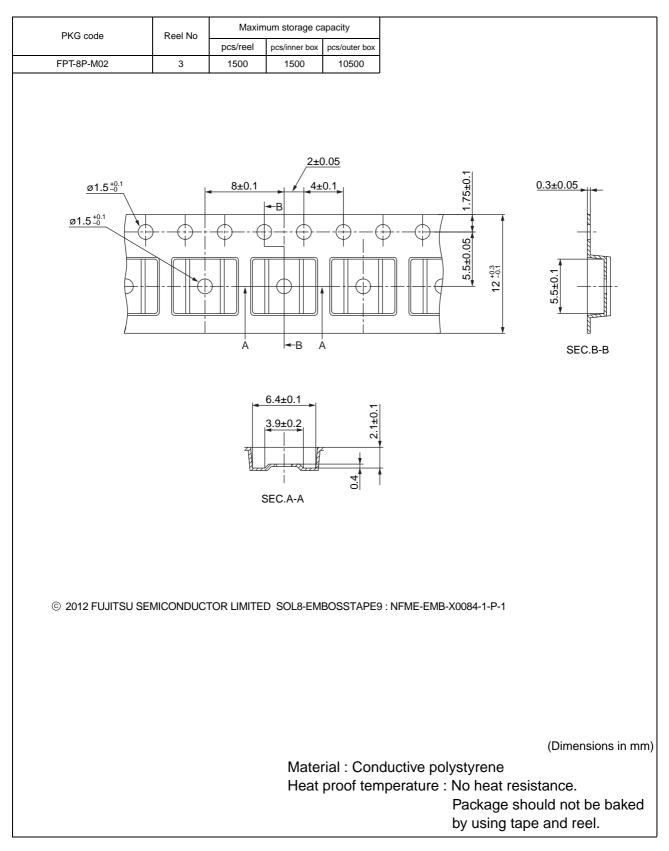


L	W	Н
565	270	180

(Dimensions in mm)

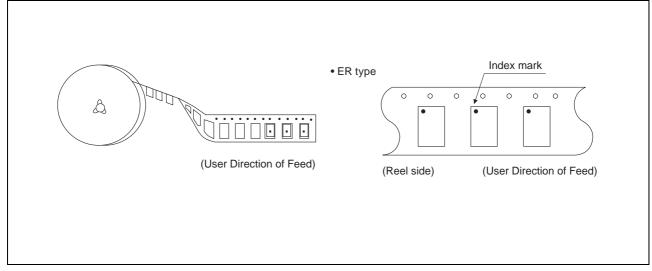
# 2. Emboss Tape

## 2.1 Tape Dimensions

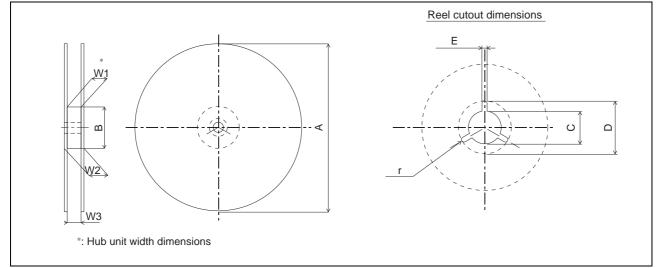


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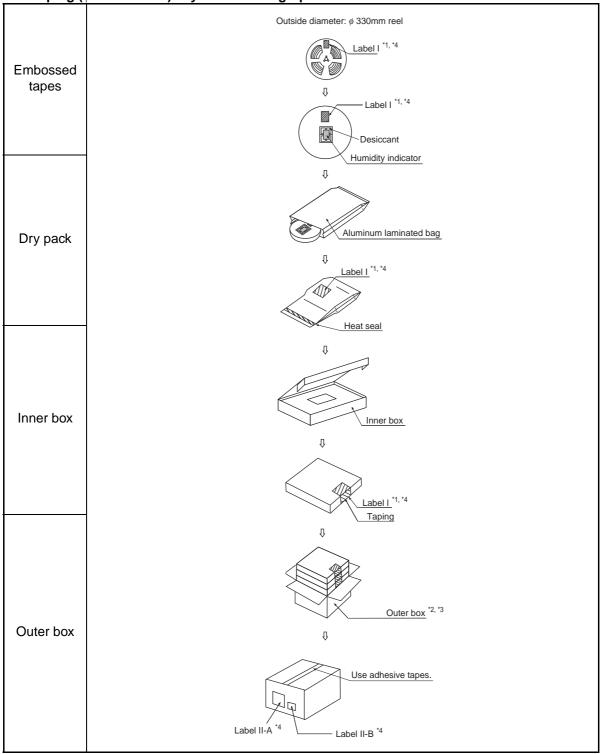
#### 2.2 IC orientation



#### 2.3 Reel dimensions



													D	imensior	ns in mm
Reel No	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
Tape width Symbol	8	1	2	1	6	2	4	3	2	4	4	56	12	16	24
A	254 ± 2	254 ± 2	330 ± 2	254 ± 2	330 ± 2	254 ± 2	330 ± 2				330	± 2			
В				1	00 <del>+2</del>			100 +2	150 <sup>+2</sup>	100 +2	150 <sup>+2</sup> -0	100 -0		100 ± 2	
С	13 ± 0.2							13 <sup>+0.5</sup> -0.2							
D	21 ± 0.8							20.5 <sup>+1</sup> <sub>-0.2</sub>							
E								2 ± 0.5							
W1	$8.4_{\cdot 0}^{+2} \qquad 12.4_{\cdot 0}^{+2} \qquad 16.4_{\cdot 0}^{+2} \qquad 24.4_{\cdot 0}^{+2} \qquad 32.4_{\cdot 0}^{+2} \qquad 44.4_{\cdot 0}^{+2} \qquad 56.4_{\cdot 0}^{+2}$							12.4 +1	16.4 +1	24.4+0.1					
W2	less than 14.4	less that	an 18.4	less th	an 22.4	less the	less than 30.4 less than 38.4 less than 50.4 less than 62.4				less than 18.4	less than 22.4	less than 30.4		
W3	7.9 ~ 10.9	11.9 -	- 15.4	15.9	~ 19.4	23.9	~ 27.4	31.9 ~ 35.4		43.9 ~	47.4	55.9 ~ 59.4	12.4 ~ 14.4	16.4 ~ 18.4	24.4 ~ 26.4
r	1.0						•								



## 2.4 Taping (\u03b330mm Reel) Dry Pack Packing Specifications

- \*1: For a product of witch part number is suffixed with "E1", a " G (R)" marks is display to the moisture barrier bag and the inner boxes.
- \*2: The size of the outer box may be changed depending on the quantity of inner boxes.
- \*3: The space in the outer box will be filled with empty inner boxes, or cushions, etc.
- \*4: Please refer to an attached sheet about the indication label.

Note: The packing specifications may not be applied when the product is delivered via a distributer.

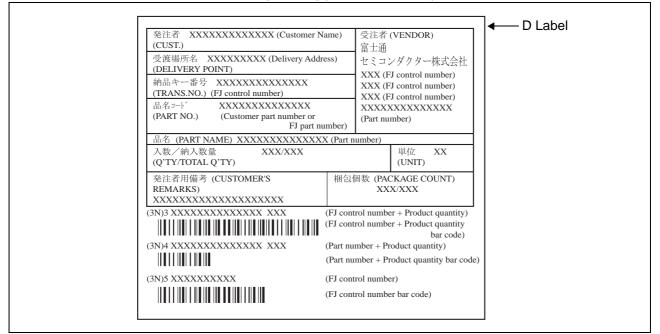


#### 2.5 Product label indicators

Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]

XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX	← C-3 Label
(3N)1 XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX	
(3N)2 XXXXXXXX XXXXXXXXXXXXXXXXXXXXXXXXXXX	
XXX pcs (Quantity) XXXXXXXXXXXXXXX (Customer part number or FJ part number)	
bar code) XXXX/XX/XX (Packed years/month/day) ASSEMBLED IN xxxx	Perforated line
XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX	<ul> <li>Supplemental Label</li> </ul>
XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX	

Label II-A: Label on Outer box [D Label] (100mm × 100mm)



#### Label II-B: Outer boxes product indicate

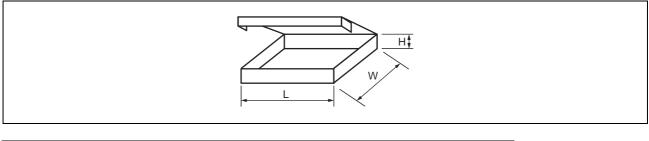
XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX	Part number)		
(Lot Number) XXXX-XXX XXXX-XXX	(Count) X箱 X箱 計	(Quantity) XXX 個 XXX 個 XXX 個	

Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

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## 2.6 Dimensions for Containers

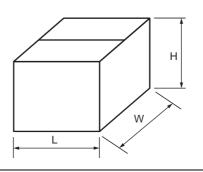
## (1) Dimensions for inner box



Tape width	L	W	н
12, 16			40
24, 32	365	345	50
44		545	65
56			75

(Dimensions in mm)

## (2) Dimensions for outer box



L	W	Н
415	400	315

(Dimensions in mm)

# ■ MAJOR CHANGES IN THIS EDITION

A change on a page is indicated by a vertical line drawn on the left side of that page.

Page	Section	Change Results
1	■ FEATURES	Revised the Data retention 10 years ( + 85 °C) →10 years ( + 85 °C), 95 years ( + 55 °C), over 200 years ( + 35 °C)
14	■ POWER ON/OFF SEQUENCE	Revised the following description: "POWER ON SEQUENCE" $\rightarrow$ "POWER ON/OFF SEQUENCE" Added the following description: "If the device does not operate within the specified conditions of read cycle, write cycle or power on/off sequence, memory data can not be guaranteed." Revised the following description: "V <sub>DD</sub> pin is required to be rising from 0 V because turning the pow- er on from an intermediate level may cause malfunctions, when the power is turned on" $\rightarrow$ "If V <sub>DD</sub> falls down below 2.0V, V <sub>DD</sub> is required to be started from 0V to prevent malfunctions when the power is turned on again."
	■ FRAM CHARACTERISTICS	Revised the table and Note



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